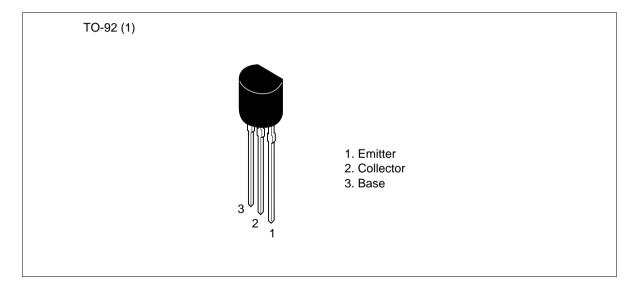
Silicon PNP Epitaxial

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#### Application

High voltage medium speed switching

#### Outline





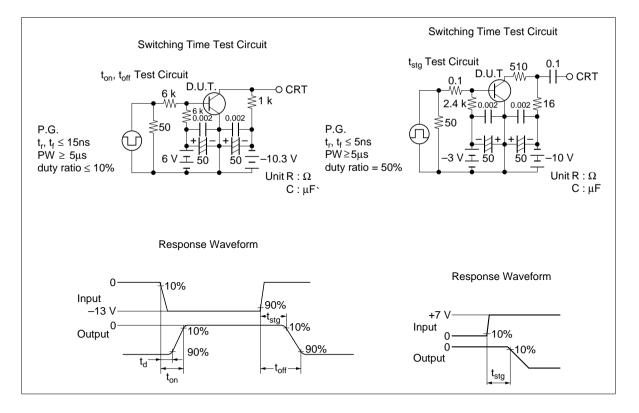
## **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

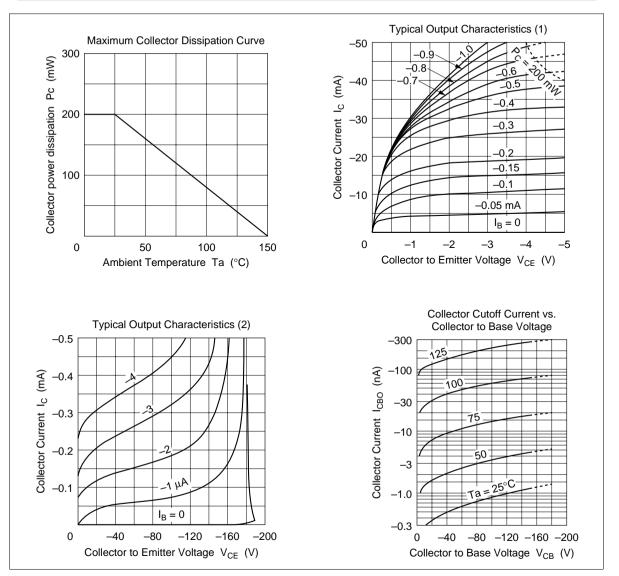
| Item                         | Symbol           | 2SA778(K)   | 2SA778A(K)  | Unit |
|------------------------------|------------------|-------------|-------------|------|
| Collector to base voltage    | V <sub>CBO</sub> | -150        | -180        | V    |
| Collector to emitter voltage | V <sub>CEO</sub> | -150        | -180        | V    |
| Emitter to base voltage      | V <sub>EBO</sub> | -5          | -5          | V    |
| Collector current            | I <sub>c</sub>   | -50         | -50         | mA   |
| Collector power dissipation  | Pc               | 200         | 200         | mW   |
| Junction temperature         | Tj               | 150         | 150         | °C   |
| Storage temperature          | Tstg             | -55 to +150 | -55 to +150 | °C   |

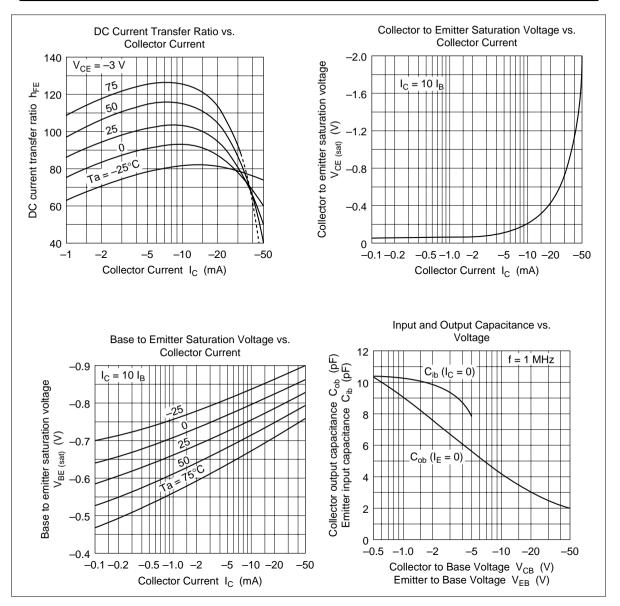
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

|   |                      | 2SA7 | 78(K) |      | 2SA778A(K) |       |      |      |  |
|---|----------------------|------|-------|------|------------|-------|------|------|--|
| Item                                    | Symbol               | Min  | Тур   | Max  | Min        | Тур   | Max  | Unit | Test conditions  |
| Collector to base breakdown voltage     | $V_{\rm (BR)CBO}$    | -150 |       | _    | -180       | _     |      | V    | $I_{c} = -50 \ \mu A, \ I_{e} = 0$   |
| Collector to emitter breakdown voltage  | $V_{\rm (BR)CER}$    | -150 | _     | —    | -180       | —     | —    | V    | $I_c = -50 $ μA,<br>R <sub>BE</sub> = 30 kΩ                                    |
| Collector cutoff current                | I <sub>cbo</sub>     | _    | —     | -1.0 |            | _     |      | μΑ   | $V_{CB} = -100 \text{ V}, I_{E} = 0$   |
|   |                      |      | —     | —    |            |       | -1.0 | μΑ   | $V_{CB} = -150 \text{ V}, \text{ I}_{E} = 0$                                   |
| Emitter cutoff current                  | I <sub>EBO</sub>     |      | _     | -1.0 |            | _     | -1.0 | μΑ   | $V_{\text{EB}} = -5 \text{ V}, \text{ I}_{\text{C}} = 0$                       |
| DC current transfer ratio               | h <sub>FE</sub>      | 30   | 100   | _    | 40         | 100   | 200  |      | V <sub>ce</sub> = -3 V,<br>I <sub>e</sub> = -15 mA                             |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | —    | -0.3  | -1.0 | _          | -0.3  | -1.0 | V    | I <sub>c</sub> = −15 mA,<br>I <sub>B</sub> = −1 mA                             |
| Base to emitter saturation voltage      | $V_{\text{BE(sat)}}$ | _    | -0.77 | -1.0 | —          | -0.77 | -1.0 | V    | $I_{c} = -15 \text{ mA},$<br>$I_{B} = -1 \text{ mA}$                           |
| Collector output capacitance            | Cob                  | _    | _     | 10   | —          | _     | 10   | pF   | $V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0,$<br>f = 1 MHz                      |
| Gain bandwidth product                  | f <sub>T</sub>       | _    | 50    | _    | —          | 50    | —    | MHz  | $V_{ce} = -3 V,$<br>$I_c = -15 mA$   |
| Turn on time                            | t <sub>on</sub>      |      | 135   | —    |            | 135   |      | ns   | $V_{cc} = -10.3 V$   |
| Turn off time                           | t <sub>off</sub>     | _    | 1.7   | _    | _          | 1.7   | —    | μs   | $I_{c} = 10 I_{B1} = -10$<br>$I_{B2} = -10 \text{ mA}$                         |
| Storage time                            | t <sub>stg</sub>     |      | _     | 1.0  | _          | _     | 1.0  | μs   | $V_{cc} = -10 V,$<br>$I_{c} = -17 mA$<br>$I_{B1} = -1mA,$<br>$I_{B2} = -12 mA$ |

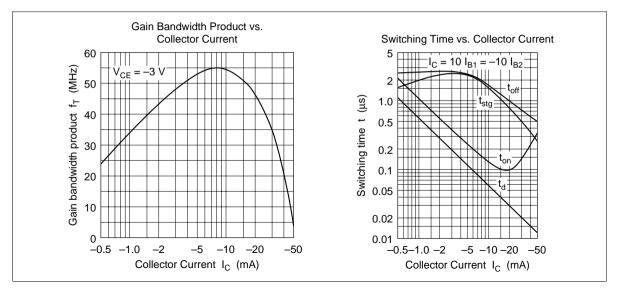
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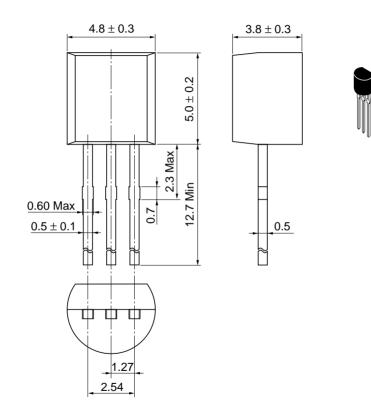




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| Hitachi Code             | TO-92 (1) |
|--------------------------|-----------|
| JEDEC                    | Conforms  |
| EIAJ                     | Conforms  |
| Weight (reference value) | 0.25 g    |

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